

SCHOTTKY BARRIER (DOUBLE) DIODE

LBAS70*LT1



Features

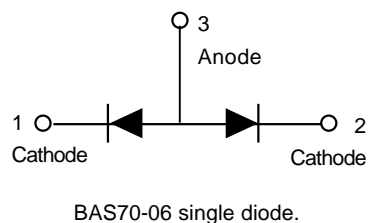
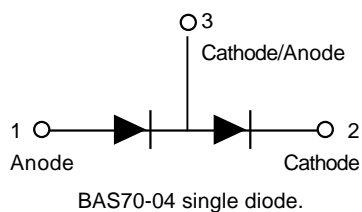
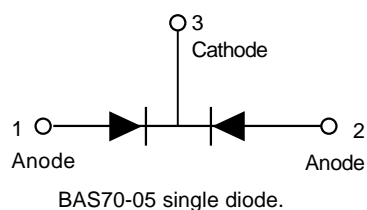
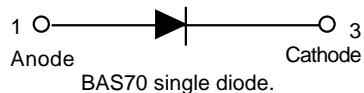
- Low forward current
- High breakdown voltage
- Guard ring protected
- Low diode capacitance.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits.

DESCRIPTION

Planar Schottky barrier diodes with an integrated guard ring for stress protection. Single diodes and double diodes with different pinning are available.



LBAS70 Series

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit	Conditions
Continuous reverse voltage	V_R	–	70	V	
Continuous forward current	I_F	–	70	mA	
Repetitive Peak forward surge current	I_{FSM}	–	70	mA	$t_p \leq 1\text{s}; \delta \leq 0.5$
Non-repetitive peak forward current	I_{FSM}	–	100	mA	$t_p < 10\text{ms}$
Storage temperature	T_{stg}	-65	+150	$^\circ\text{C}$	
Junction temperature	T_j	–	150	$^\circ\text{C}$	
Operating ambient temperature	T_{amb}	-65	+150	$^\circ\text{C}$	

DEVICE MARKING

LBAS70LT1=BE LBAS70-04LT1=CG LBAS70-05LT1=EH LBAS70-06LT1=GK

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Max.	Unit	Conditions
Forward voltage(Fig.3)	V_F	410	mV	$I_F=1\text{mA}$
		750	mV	$I_F=10\text{mA}$
		1	v	$I_F=15\text{mA}$
Reverse current(Fig.4 ;note1)	I_R	100	nA	$V_R=50\text{V}$
		10	μA	$V_R=70\text{V}$
Charge carrier life time (krakauer method)	τ	100	ps	$I_F=5\text{mA}$
Diode capacitance(Fig.6)	C_d	2	pF	$f=1\text{MHz}; V_R=0$

Note:

1. Pulse test: $t_p=300\mu\text{s}; \delta=0.02$.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT	CONDITIONS
Thermal resistance from junction to ambient	$R_{th\ j-a}$	500	k/w	note1

Note

1. Refer to SOT23 or SOT143B standard mounting conditions.

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Electrical characteristic curves($T_A = 25^\circ\text{C}$)

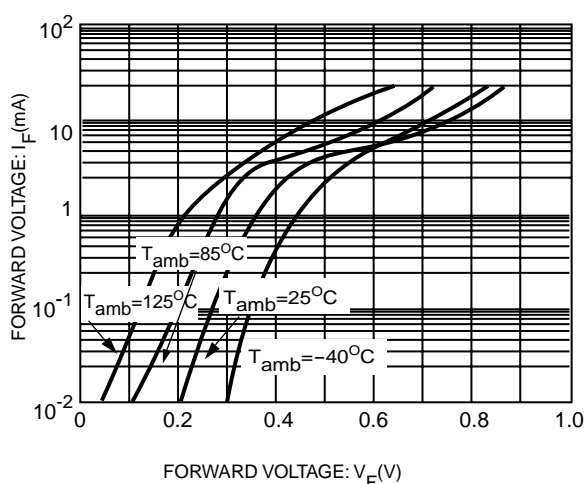


Fig.1 Forward current as a function of forward voltage; typical values.

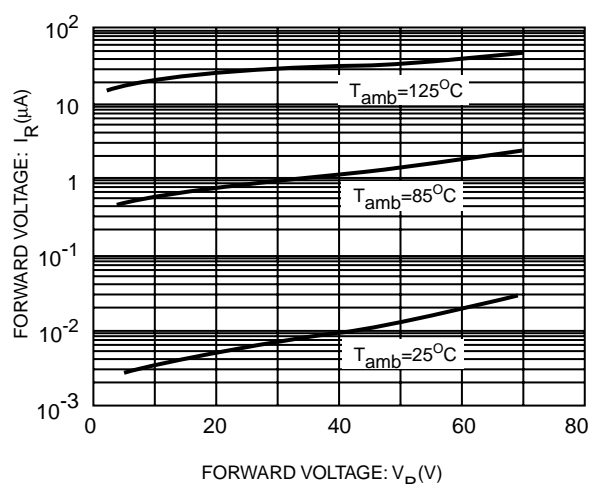


Fig.2 Reverse current as a function of reverse voltage; typical values.

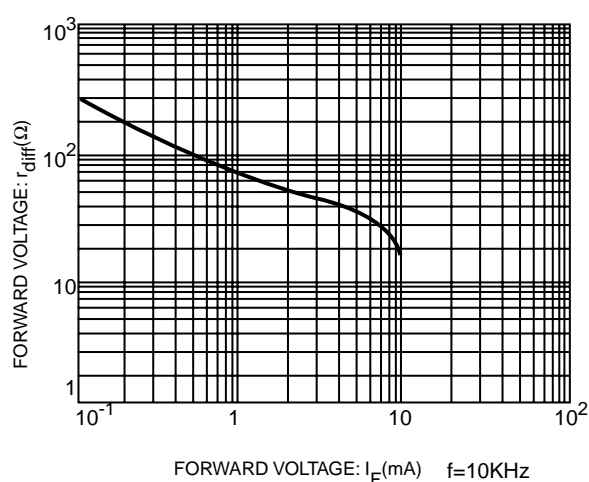


Fig.3 Differential forward resistance as a function of forward current; typical values.

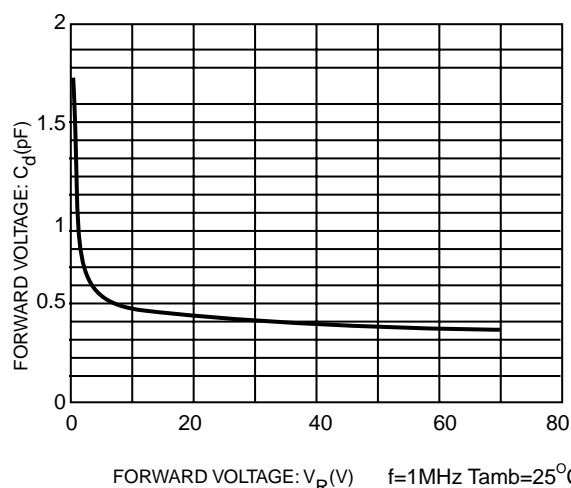


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

LBAS70 Series

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

